

CLC1003

Low Distortion, Low Offset, RRIO Amplifier

General Description

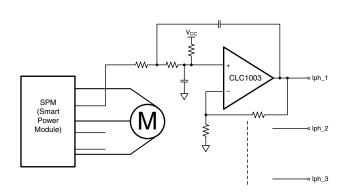
The CLC1003 is a single channel, high-performance, voltage feedback amplifier with near precision performance, low input voltage noise, and ultra low distortion. The CLC1003 offers 1mV maximum input offset voltage, 3.5nV/JHz broadband input voltage noise, and 0.00005% THD at 1kHz. These amplifiers also provide 55MHz gain bandwidth product and 12V/µs slew rate making them well suited for applications requiring precision DC performance and high AC performance. This high-performance amplifier also offers a rail-to-rail input and output, simplifying single supply designs and offering larger dynamic range possibilities. The inputs extend beyond the rails by 500mV.

The CLC1003 is designed to operate from 2.5V to 12V supplies and operate over the extended temperature range of 40°C to +125°.

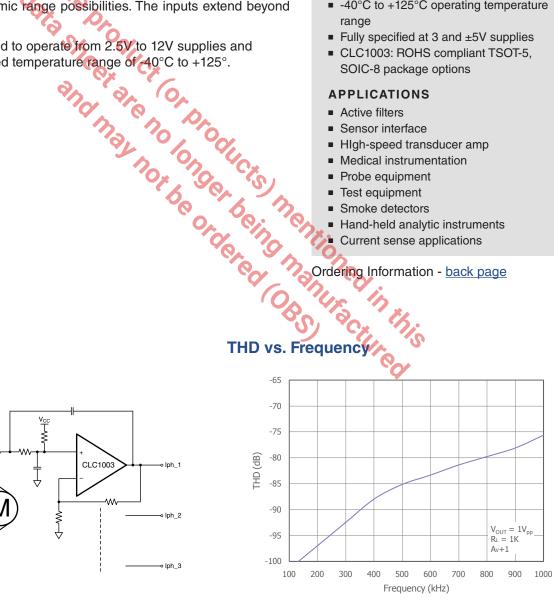
FEATURES

- 1mV maximum input offset voltage
- 0.00005% THD at 1kHz
- 5.3nV/JHz input voltage noise > 10kHz
- -90dB/-85dB HD2/HD3 at 100kHz, $R_1 = 100\Omega$
- <-100dB HD2 and HD3 at 10kHz, $R_1 = 1k\Omega$
- Rail-to-rail input and output
- 55MHz unity gain bandwidth
- 12V/us slew rate
- +80mA, -55mA output current
- -40°C to +125°C operating temperature
- Fully specified at 3 and ±5V supplies
- CLC1003: ROHS compliant TSOT-5,

Typical Application



Current Sensing in 3-Phase Motor



Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V _S	0V to +14V
V _{IN} V _S - 0.5V t	0.5V + 0.5V

Operating Conditions

Supply Voltage Range	2.5V to 12V
Operating Temperature Range	40°C to 125°C
Junction Temperature	150°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10s)	260°C

Package Thermal Resistance

	θ _{JA} (TSOT-5)	215°C/W
	θ _{JA} (SOIC-8)	150°C/W
data sheet are no long and may no to be one	Package thermal resistance $(\theta_{\mbox{\scriptsize JA}}),$ JEDEC standard, test boards, still air.	multi-layer
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Electrical Characteristics at +3V

 T_A = 25°C, V_S = +3V, R_f = 1k $\Omega,\,R_L$ = 1k Ω to $V_S/2;\,G$ = 2; unless otherwise noted.

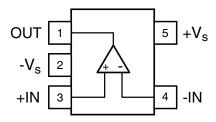
Symbol	Parameter	Conditions	Min	Тур	Max	Units			
Frequency [Frequency Domain Response								
GBWP	-3dB Gain Bandwidth Product	$G = 10, V_{OUT} = 0.05V_{pp}$		31		MHz			
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.05V_{pp}, R_f = 0$		50		MHz			
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.05V_{pp}$		24		MHz			
BW _{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		3.3		MHz			
Time Domai	n			\\					
t _R , t _F	Rise and Fall Time	V _{OUT} = 2V step; (10% to 90%)		150		ns			
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		78		ns			
OS	Overshoot	V _{OUT} = 2V step		0.3		%			
SR	Slew Rate	2V step		11		V/µs			
Distortion/N	oise Response								
LIDO	O ALLA STATE OF THE STATE OF TH	$2V_{pp}$, $10kHz$, $R_L = 1k\Omega$		-98		dBc			
HD2	2nd Harmonic Distortion	$^{2}V_{pp}$, 100kHz, R _L = 100Ω		-85		dBc			
LIDO	Out II amount a Bistontian	$2V_{pp}$, 10kHz, R _L = 1kΩ		-95		dBc			
HD3	3rd Harmonic Distortion	$2V_{pp}$, 100kHz, R _L = 100Ω		-81		dBc			
THD	Total Harmonic Distortion	$1V_{pp}$, 1kHz, G = 1, R _L = 2k Ω		0.0005		%			
		S10kHz		5.5		nV/√Hz			
e _n	Input Voltage Noise	>100kHz		3.9		nV/√Hz			
DC Perform	ance	/ 9/		,		,			
V _{IO}	Input Offset Voltage	12 12 1C+		0.088		mV			
d _{VIO}	Average Drift	10 00 V		1.3		μV/°C			
I _B	Input Bias Current	00 11 12		-0.340		μΑ			
dl _B	Average Drift	0.00.00		0.8		nA/°C			
I _{OS}	Input Offset Current	(c) (D) (1);		0.2		μΑ			
PSRR	Power Supply Rejection Ratio	DC Q Q		100		dB			
A _{OL}	Open Loop Gain	V _{OUT} = V _S / 2		104		dB			
I _S	Supply Current	per channel		1.85		mA			
Input Chara	cteristics	100 45 4	2			,			
R _{IN}	Input Resistance	Non-inverting, G = 1	%:	30		MΩ			
C _{IN}	Input Capacitance	9 7	· ·	1.1		pF			
CMIR	Common Mode Input Range		0.	-0.5 to 3.5		V			
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0.5V to 2.5V	Q	94		dB			
Output Chai	acteristics								
V _{OUT}	Output Swing	$R_L = 150\Omega$		0.085 to 2.80		V			
VOUT	Output Swilly	$R_L = 1k\Omega$		0.04 to 2.91		V			
l _{out}	Output Current			+75, -40		mA			
I _{SC}	Short Circuit Current	$V_{OUT} = V_S / 2$		+95, -50		mA			

Electrical Characteristics at ±5V

 T_A = 25°C, V_S = ±5V, R_f = 1k $\Omega,\,R_L$ = 1k Ω to GND; G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = 10, V_{OUT} = 0.05V_{pp}$		35		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.05V_{pp}, R_f = 0$		55		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.05V_{pp}$		25		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		3.6		MHz
Time Doma	in					
t _R , t _F	Rise and Fall Time	V _{OUT} = 2V step; (10% to 90%)		125		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		80		ns
OS	Overshoot	V _{OUT} = 2V step		0.3		%
SR	Slew Rate	4V step		12		V/µs
Distortion/N	loise Response					
LIDO	On all la maria Distration Population	$2V_{pp}$, $10kHz$, $R_L = 1k\Omega$		-125		dBc
HD2	2nd Harmonic Distortion	$2V_{pp}$, 100kHz, R _L = 100 Ω		-90		dBc
LIDO	Out Hammania Distantian	$2V_{pp}$, 10kHz, $R_L = 1k\Omega$		-127		dBc
HD3	3rd Harmonic Distortion	$2V_{pp}$, 100kHz, $R_L = 100Ω$		-85		dBc
THD	Total Harmonic Distortion	$1V_{pp}$, $1kHz$, $G = 1$, $R_L = 2k\Omega$		0.00005		%
		10kHz		5.3		nV/√Hz
e _n	Input Voltage Noise	>100kHz		3.5		nV/√Hz
DC Perform	nance	6 %		'		,
V _{IO}	Input Offset Voltage	12 0 C+	-1	0.050	1	mV
d _{VIO}	Average Drift	10 C		1.3		μV/°C
I _B	Input Bias Current	00 11 12	-2.6	-0.30	2.6	μΑ
dl _B	Average Drift	0.00.00		0.85		nA/°C
Ios	Input Offset Current	Col Do Tr.		0.2	0.7	μΑ
PSRR	Power Supply Rejection Ratio	DC OA	82	100		dB
A _{OL}	Open Loop Gain	V _{OUT} = V _S /2	95	115		dB
I _S	Supply Current	per channel		2.2	2.75	mA
Input Chara	acteristics	000	7			
R _{IN}	Input Resistance	Non-inverting, G = 1	%.	30		ΜΩ
C _{IN}	Input Capacitance	2	S	1		pF
CMIR	Common Mode Input Range		0	±5.5		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = -3V to 3V	70	95		dB
Output Cha	racteristics					,
V _{OUT}	Output Swing	R _L = 150Ω		-4.826 to 4.534		V
• 001		$R_L = 1k\Omega$	-4.7	-4.93 to 4.85	4.7	V
I _{OUT}	Output Current			+80, -55		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S / 2$		+115, -90		mA

CLC1003 Pin Configurations TSOT-5

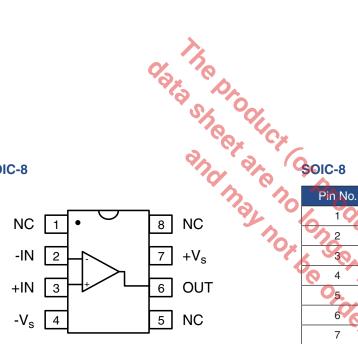


CLC1003 Pin Assignments

TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-V _S	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V _S	Positive supply

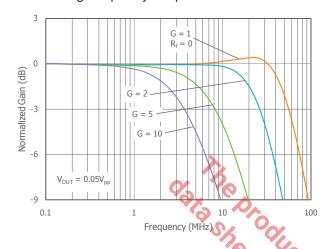
SOIC-8



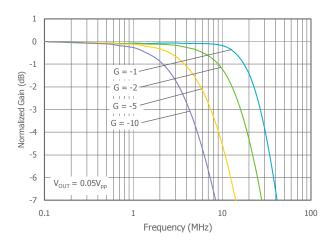
	Pin No.	Pin Name	Description
	10/	NC	No Connect
	2	-IN	Negative input
	30	+IN	Positive input
4	0 4 6	-V _S	Negative supply
	0 5.	NC	No Connect
	6	OUT	Output
	7	+V _S	Positive supply
	8	NC NC	No Connect

 $T_A = 25$ °C, $V_S = \pm 5V$, $R_f = 1k\Omega$, $R_L = 1k\Omega$, G = 2; unless otherwise noted.

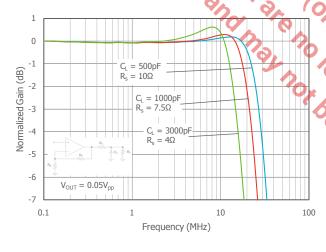
Non-Inverting Frequency Response



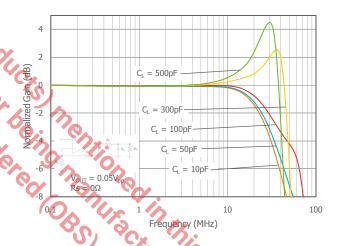
Inverting Frequency Response



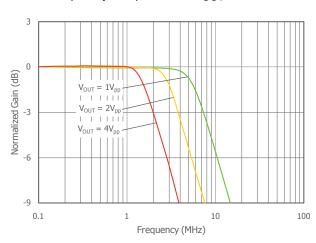
Frequency Response vs. C_L



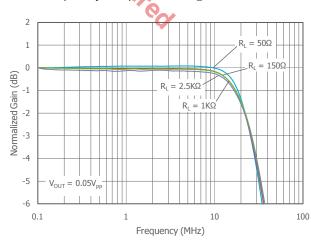
Frequency Response vs. CI without RS



Frequency Response vs. V_{OUT}

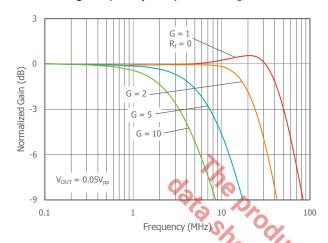


Frequency Response vs. R_L

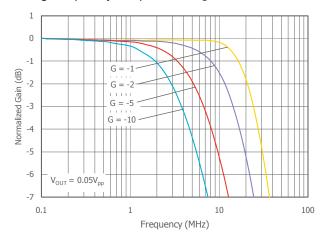


 T_A = 25°C, V_S = ±5V, R_f = 1k $\Omega,~R_L$ = 1k $\Omega,~G$ = 2; unless otherwise noted.

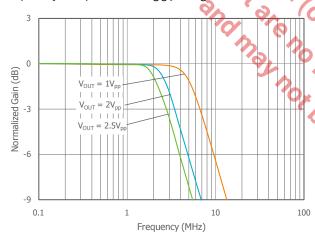
Non-Inverting Frequency Response at $V_S = 3V$



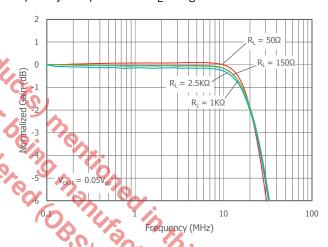
Inverting Frequency Response at $V_S = 3V$



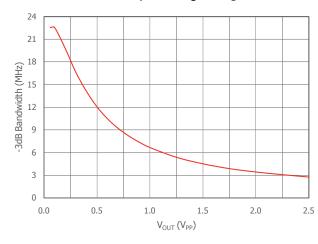
Frequency Response vs. V_{OUT} at V_S = 3V



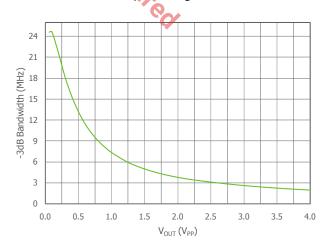
Frequency Response vs. R_L at $V_S = 3V$



-3dB Bandwidth vs. Output Voltage at $V_S = 3V$

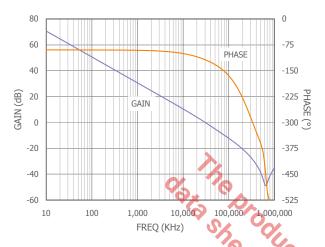


-3dB Bandwidth vs. Output Voltage

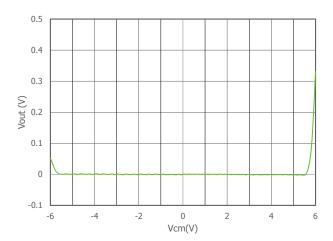


 T_A = 25°C, V_S = ±5V, R_f = 1k $\Omega,~R_L$ = 1k $\Omega,~G$ = 2; unless otherwise noted.

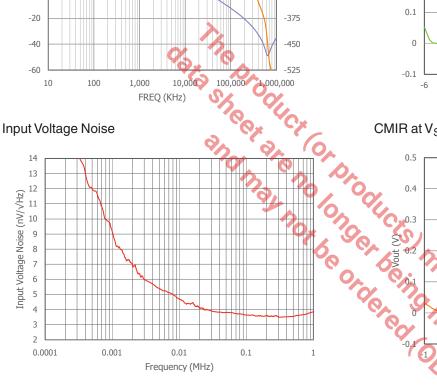
Open Loop Gain and Phase vs.



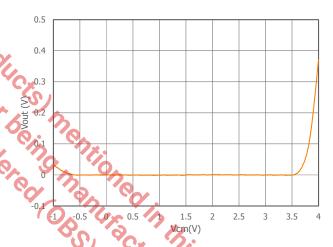
CMIR



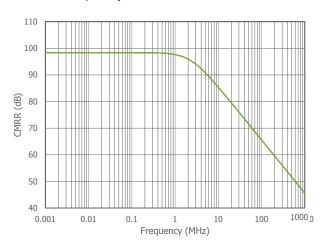
Input Voltage Noise



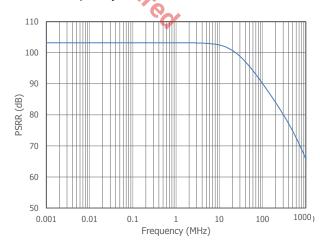
CMIR at $V_S = 3V$



CMRR vs. Frequency

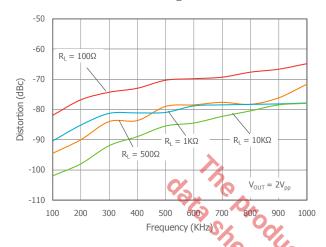


PSRR vs. Frequency

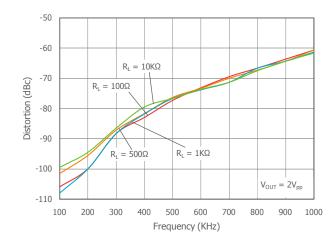


 T_A = 25°C, V_S = ±5V, R_f = 1k $\Omega,~R_L$ = 1k $\Omega,~G$ = 2; unless otherwise noted.

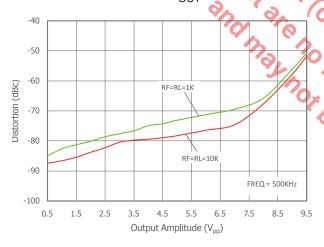
2nd Harmonic Distortion vs. R_L

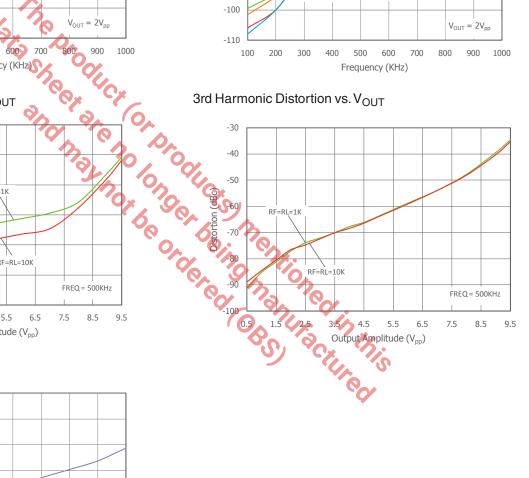


3rd Harmonic Distortion vs. RL

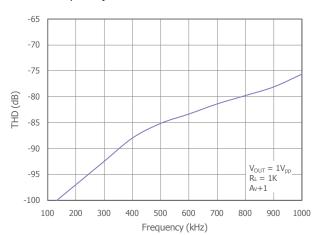


2nd Harmonic Distortion vs. V_{OUT}



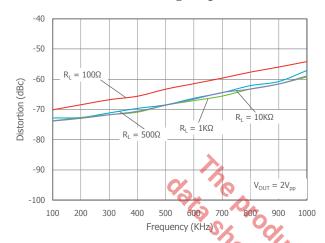


THD vs. Frequency

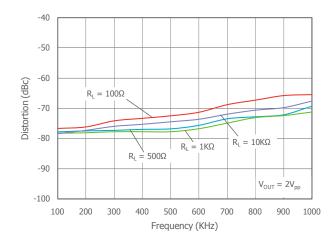


 T_A = 25°C, V_S = ±5V, R_f = 1k $\Omega,~R_L$ = 1k $\Omega,~G$ = 2; unless otherwise noted.

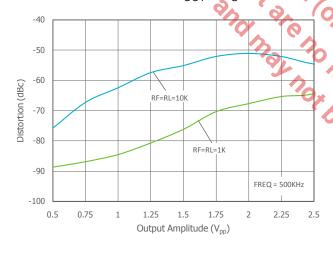
2nd Harmonic Distortion vs. R_L at $V_S = 3V$



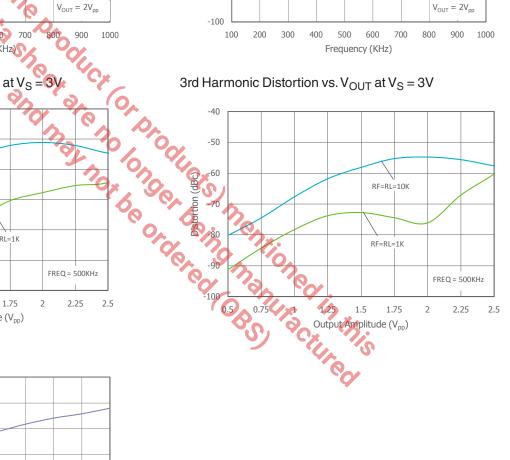
3rd Harmonic Distortion vs. R_L at $V_S = 3V$



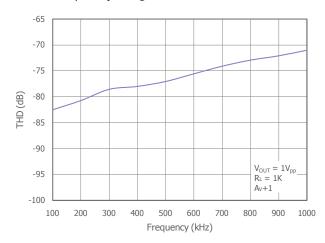
2nd Harmonic Distortion vs. V_{OUT} at V_{S}



3rd Harmonic Distortion vs. V_{OUT} at $V_S = 3V$

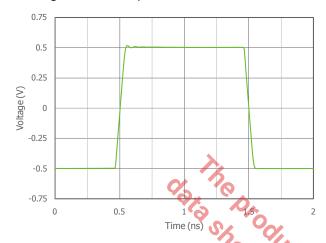


THD vs. Frequency at $V_S = 3V$

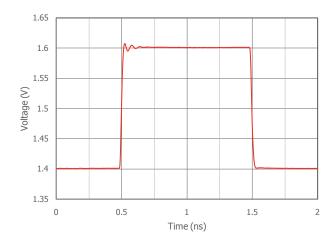


 $T_A = 25$ °C, $V_S = \pm 5$ V, $R_f = 1$ k Ω , $R_L = 1$ k Ω , G = 2; unless otherwise noted.

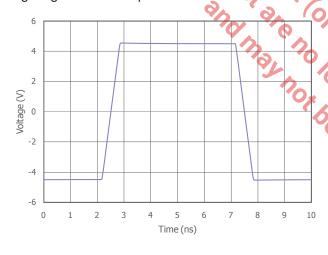
Small Signal Pulse Response



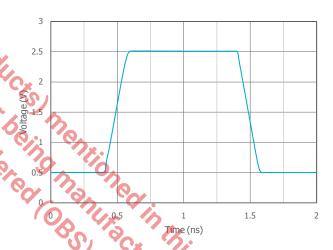
Small Signal Pulse Response at $V_S = 3V$



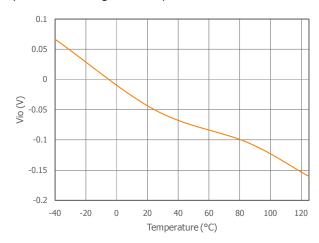
Large Signal Pulse Response



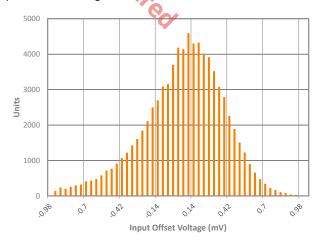
Large Signal Pulse Response at $V_S = 3V$



Input Offset Voltage vs. Temperature



Input Offset Voltage Distribution



Application Information

Basic Information

Figures 1 and 2 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations.

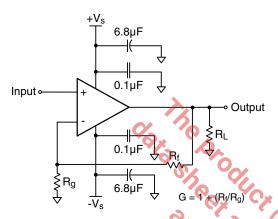


Figure 1: Typical Non-Inverting Gain Circuit

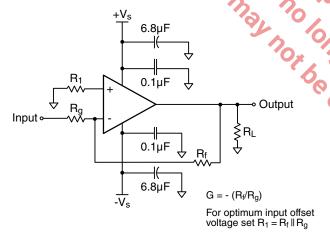


Figure 2: Typical Inverting Gain Circuit

Power Dissipation

Power dissipation should not be a factor when operating under the stated 500Ω load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 150°C. To calculate the junction temperature, the package thermal resistance value Theta_JA (θ_{JA}) is used along with the total die power dissipation.

$$T_{\text{Junction}} = T_{\text{Ambient}} + (\theta_{\text{JA}} \times P_{\text{D}})$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D, the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{load}$$

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMSsupply}}$$

 $V_{\text{supply}} = V_{\text{S+}} - V_{\text{S-}}$

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{load})_{RMS^2})/Rload_{eff}$$

The effective load resistor (Rload_{eff}) will need to include the effect of the feedback network. For instance,

Rloadeff in Figure 2 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, Pp can be found from

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(V_{load})_{RMS} = V_{peak} / \sqrt{2}$$

 $(I_{load})_{RMS} = (V_{load})_{RMS} / Rload_{eff}$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{Dynamic} = (V_{S+} - V_{load})_{RMS} \times (I_{load})_{RMS}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

Figure 3 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

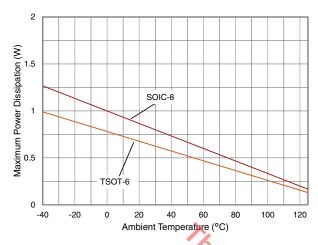


Figure 3. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, RS, between the amplifier and the load to help improve stability and settling performance. Refer to Figure 4

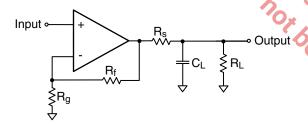


Figure 4. Addition of R_S for Driving Capacitive Loads

The CLC1003 is capable of driving up to 300pF directly, with no series resistance. Directly driving 500pF causes over 4dB of frequency peaking, as shown in the plot on page 6. Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in ≤ 1dB peaking in the frequency response. The Frequency Response vs. C_L plots, on page 6, illustrate the response of the CLC1003.

C _L (pF)	R _S (Ω)	-3dB BW (MHz)
500	10	27
1000	7.5	20
3000	4	15

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Overdrive Recovery

An overdrive condition is defined as the point when either one of the inputs or the output exceed their specified voltage range. Overdrive recovery is the time needed for the amplifier to return to its normal or linear operating point. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The CLC1003 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the CLC1003 in an overdriven condition.

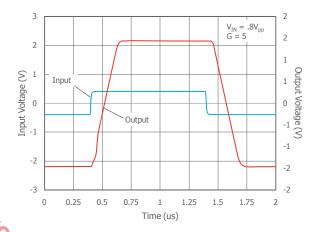


Figure 5: Overall ut Considerations for Offset and Noise Performance

There are three sources of offset contribution to consider; input bias current, input bias current mismatch, and input offset voltage. The input bias currents are assumed to be equal with and additional offset current in one of the inputs to account for mismatch. The bias currents will not affect the offset as long as the parallel combination of Rf and Rg matches R_t. Refer to Figure 6/

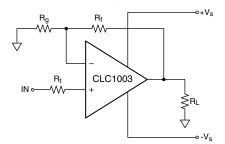


Figure 6: Circuit for Evaluating Offset

The first place to start is to determine the source resistance. If it is very small an additional resistance may need to be added to keep the values of $R_{\mbox{\scriptsize f}}$ and $R_{\mbox{\scriptsize q}}$ to practical levels. For this analysis we assume that Rt is the total resistance present on the non-inverting input. This gives us one equation that we must solve:

$$R_t = R_0 II R_f$$

This equation can be rearranged to solve for R_a:

$$R_{q} = (R_{t} * R_{f}) / (R_{f} - R_{t})$$

The other consideration is desired gain (G) which is:

$$G = (1 + R_f/R_0)$$

By plugging in the value for Rq we get

$$R_f = G * R_t$$

And R_a can be written in terms of R_t and G as follows:

$$R_0 = (G * R_t) / (G - 1)$$

The complete input offset equation is now only dependent on the voltage offset and input offset terms given by:

$$VI_{OS} = \sqrt{\left(V_{IO}\right)^2 + \left(I_{OS} \cdot RT\right)^2}$$

And the output offset is:

$$VO_{OS} = G * \sqrt{(V_{IO})^2 + (I_{OS} * RI)^2}$$

Noise analysis

The complete equivalent noise circuit is shown in Figure 7.

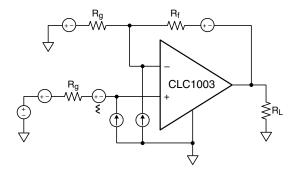


Figure 7: Complete Equivalent Noise Circuit

The complete noise equation is given by:

$$v_o^2 = v_{orext}^2 + \left(e_n \left(1 + \frac{RF}{RG}\right)\right)^2 + \left(i_{bp} * RT \left(1 + \frac{RF}{RG}\right)\right)^2 + \left(i_{bn} * RF\right)^2$$

Where V_{orext} is the noise due to the external resistors and is given by:

$$v_o^2 = \left(e_n \left(1 + \frac{RF}{RG}\right)\right)^2 + \left(e_G * \frac{RF}{RG}\right)^2 + e_F^2$$

The complete equation can be simplified to:

$$v_0^2 = 3*(4kT*G*RT) + (e_nG)^2 + 2*(i_n*RT)^2$$

It's easy to see that the effect of amplifier voltage noise is proportionate to gain and will tend to dominate at large gains. The other terms will have their greatest impact at large Rt values at lower gains.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Exar has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Minn.

 Refer to the information. Remove the ground plane under and around the part. especially near the input and output pins to reduce parasitic capacitance
 - Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more

Evaluation Board Information

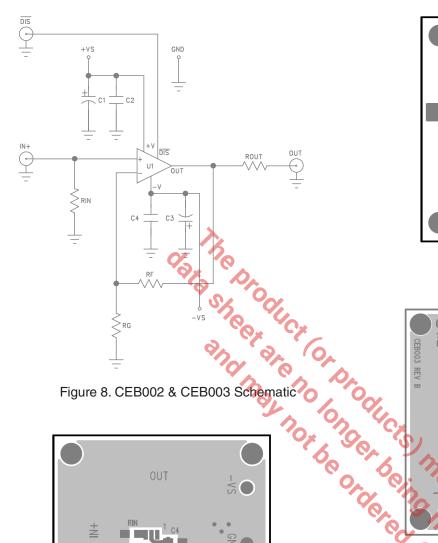
The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board #	Products
CEB002	CLC1003 in TSOT
CEB003	CLC1003 in SOIC

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 8-12 These evaluation boards are built for dualsupply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -V_S to ground.
- 2. Use C3 and C4, if the -V_S pin of the amplifier is not directly connected to the ground plane.



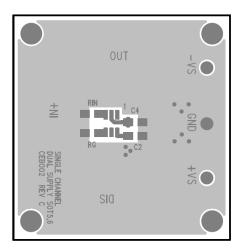


Figure 9. CEB002 Top View

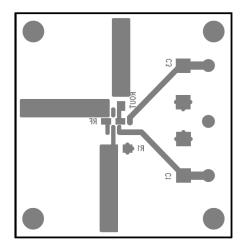


Figure 10. CEB002 Bottom View

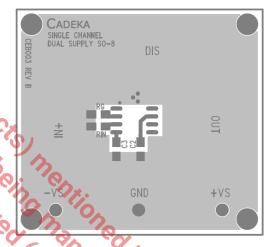


Figure 11. CEB003 Top View

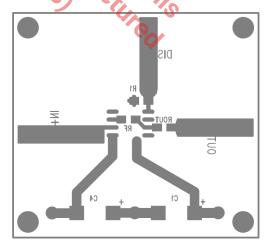
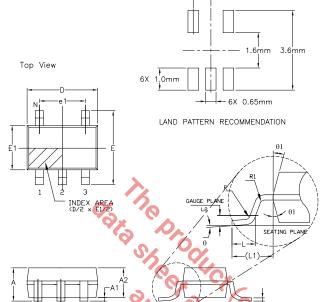


Figure 12. CEB003 Bottom View

Mechanical Dimensions





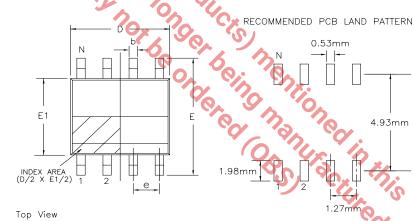
4X 0.95mm-

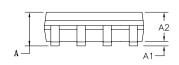
5 Pin TSOT (OPTION 2)						
SYMBOLS	DIMENSION IN MM (Control Unit)			DIMENSION IN INC (Reference Unit)		
	MIN	NOM	MAX	MIN	МОМ	MAX
Α	0.75	_	0.80	0.030	_	0.031
A1	0.00	_	0.05	0.000	_	0.002
A2	0.70	0.75	0.78	0.028	0.030	0.031
b	0.35	_	0.50	0.012	_	0.020
С	0.10	_	0.20	0.003	_	0.008
D	2	.90 BS	iC	().114 B	SC
E	2	2.80 BS	iC	().110 B	SC
E1	1	.60 BS	iC	(0.063 B	SC
е		.95 BS	iC	(0.038 B	SC
e1	1.90 BSC			0	0.075 B	SC
L	0.37	0.45	0.60	0.012	0.018	0.024
L1	0.60 REF			0	.024 RE	F
L2	0.25 BSC			0	.010 BS	SC SC
R	0.10	_	_	0.004	_	_
R1	0.10	_	0.25	0.004 — 0.010		0.010
θ	0.	4'	8*	0,	4.	8,
θ1	4.	10°	12"	4.	10°	12*
N	5 5					

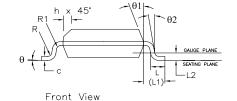
4.93mm

SOIC-8 Package

Side View







Side View

JEDEC MS-012 Variation
SIONS IN MM DIMENSIONS IN
Introl Unit) (Reference Uni

LZ	,	0.23 B3C 0.010 B3C				_
R	0.07	_		0.003	_	
R1	0.07	_		0.003	_	
θ	0,	_	8.	0.	_	8,
91	5*	_	15°	5*	_	15°
92	0,	_	_	0,		_
D	4	1.90 BSC	;	0	.193 BS	C
N		8			8	

Ordering Information

Part Number	Package	Green	Operating Temperature Range	Packaging Quantity				
CLC1003 Ordering Information								
CLC1003IST5X	TSOT-5	Yes	-40°C to +125°C	2.5k Tape & Reel				
CLC1003IST5MTR	TSOT-5	Yes	-40°C to +125°C	250 Tape & Reel				
CLC1003IST5EVB	Evaluation Board	N/A	N/A	N/A				
CLC1003ISO8X	SOIC-8	Yes	-40°C to +125°C	2.5k Tape & Reel				
CLC1003ISO8MTR	SOIC-8	Yes	-40°C to +125°C	250 Tape & Reel				
CLC1003ISO8EVB	Evaluation Board	N/A	N/A	N/A				

Moisture sensitivity level for all parts is MSL-1.

Revision History

Tievision mistory	Y/2	\mathcal{D}_{\bullet}
Revision	Date	Description
1D (ECN 1441-07)	September 2014	Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Increased "I" temperature range from +85 to +125°C. Removed "A" temp grade parts, since "I" is now equivalent. Updated thermal resistance numbers and package outline drawings.
		Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Increased "I" temperature range from +85 to +125°C. Removed "A" temp grade parts, since "I" is now equivalent. Updated thermal resistance numbers and package outline drawings.
		OBS) Required in this
For Further Assistance:		
Email: CustomerSupport@exar.com or HPATechSupport@exar.com		
Exar Technical Documentation: http://www.exar.com/techdoc/		

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